








	<h2 style="color: red;">FQB2N80TM</h2>
	Hersteller-Teilenummer: FQB2N80TM
	Hersteller / Marke: Fairchild/ON Semiconductor
	Teil der Beschreibung: MOSFET N-CH 800V 2.4A D2PAK
	Datenblätter:  FQB2N80TM.pdf
	RoHs Status: Bleifrei / RoHS-konform
	Lagerzustand: New original, 700 pcs Stock Available.
Liefern von: Hong Kong	
Versandweg: DHL/Fedex/TNT/UPS/EMS	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	FQB2N80TM
Hersteller	Fairchild/ON Semiconductor
Beschreibung	MOSFET N-CH 800V 2.4A D2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	700 pcs Stock
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D ² PAK (TO-263AB)
Verlustleistung (max)	3.13W (Ta), 85W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	800V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	2.4A (Tc)
Rds On (Max) @ Id, Vgs	6.3 Ohm @ 900mA, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	15nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	550pF @ 25V
Verpackung	Tape & Reel (TR)




















FQB2N80TM ist neu im Original, Suche FQB2N80TM Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB2N80TM Fairchild/ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB2N80TM: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>FQB2NA90TM Fairchild/ON Semiconductor MOSFET N-CH 900V 2.8A D2PAK</p>	 <p>FQB2NA90TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 900V 2.8A D2PAK</p>	 <p>FQB2N60 FAIRCHILD FQB2N60 FAIRCHILD</p>	 <p>FQB2P25TM Fairchild/ON Semiconductor MOSFET P-CH 250V 2.3A D2PAK</p>
 <p>FQB2N90TM Fairchild/ON Semiconductor MOSFET N-CH 900V 2.2A D2PAK</p>	 <p>FQB2N80 Fairchild/ON Semiconductor FQB2N80 FAIRCHILD</p>	 <p>FQB2N90TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 900V 2.2A D2PAK</p>	 <p>FQB2N80TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 800V 2.4A D2PAK</p>

heiße Teile

Mehr

 FQB19N20TM	 FQB19N20TM	 FQB1N60TM	 FQB1N60TM	 FQB20N06L
 FQB20N60FTM	 FQB20N60TM	 FQB22P10	 FQB22P10TM	 FQB22P10TM
 FQB22P10TM_F085	 FQB24N08TM	 FQB24N08TM	 FQB25N33	 FQB25N33TM
 FQB25N33TM	 FQB25N33TM_F085	 FQB27N25TM	 FQB27P06	 FQB27P06TM
 FQB27P06TM	 FQB2N50C	 FQB2N60TM	 FQB2N60TM	 FQB2N80TM
 FQB2NA90TM	 FQB2NA90TM	 FQB2P25TM	 FQB2P25TM	 FQB30N06
 FQB30N06L	 FQB30N06LTM	 FQB30N06LTM	 FQB30N06TM	 FQB30N06TM
 FQB32N12V2	 FQB32N12V2TM	 FQB32N12V2TM	 FQB32N20	 FQB32N20C
 FQB32N20CTM	 FQB32N20CTM	 FQB32N30	 FQB33N10	 FQB33N10L
 FQB33N10LTM	 FQB33N10LTM	 FQB33N10TM	 FQB33N10TM	 FQB34N20

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